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Boost chopper MOSFET Power Module

CR1

VBUS

$V_{DSS} = 500V$ $R_{DSon} = 17m\Omega \text{ typ } @ \text{ Tj} = 25^{\circ}\text{C}$ $I_D = 180\text{A} @ \text{ Tc} = 25^{\circ}\text{C}$

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
 - Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{DSS}	Drain - Source Breakdown Voltage		500	V
I _D	Continuous Drain Current	$T_c = 25^{\circ}C$	180	
ID	Continuous Drain Current	$T_c = 80^{\circ}C$	135	А
I _{DM}	Pulsed Drain current		720	
V _{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		20	mΩ
PD	Maximum Power Dissipation	$T_c = 25^{\circ}C$	1250	W
I _{AR}	Avalanche current (repetitive and non repetitive)		51	А
E _{AR}	Repetitive Avalanche Energy		50	mJ
E _{AS}	Single Pulse Avalanche Energy	Energy		ШJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$ $T_j = 25^{\circ}C$			400	μA
		$V_{GS} = 0V, V_{DS} = 400V$ $T_j = 125^{\circ}C$			2000	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 90A$		17	20	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10 \text{mA}$	3		5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		28		
C _{oss}	Output Capacitance	$V_{\rm DS} = 25 V$		5.6		nF
C _{rss}	Reverse Transfer Capacitance	f=1MHz		0.36		
Qg	Total gate Charge	$V_{GS} = 10V$		560		nC
Q _{gs}	Gate – Source Charge	$V_{Bus} = 250V$		160		
Q_{gd}	Gate – Drain Charge	$I_{\rm D} = 180 {\rm A}$		280		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		21		
Tr	Rise Time	$V_{GS} = 15V$		38		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 333V$ $I_{D} = 180A$		75		
$T_{\rm f}$	Fall Time	$R_G = 0.5\Omega$		93		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 180A, R_G = 0.5\Omega$		4140		I
E_{off}	Turn-off Switching Energy			3380		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V$, $V_{Bus} = 333V$ $I_D = 180A$, $R_G = 0.5\Omega$		6224		т
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy			4052		μJ

Chopper diode ratings and characteristics

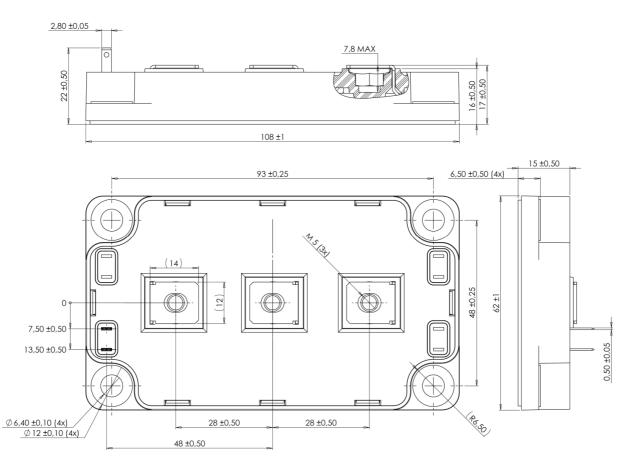
Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I _{RM}	Maximum Reverse Leakage Current	V _R =600V	$T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$			500 1000	μΑ
$I_{\rm F}$	DC Forward Current		$T_c = 70^{\circ}C$		180		Α
	Diode Forward Voltage	$I_{\rm F} = 180 {\rm A}$			1.6	1.8	
$V_{\rm F}$		$I_F = 360A$			1.9		V
		$I_{\rm F} = 180 {\rm A}$	$T_{j} = 125^{\circ}C$		1.4		
t _{rr}	Reverse Recovery Time	x 100.1	$T_j = 25^{\circ}C$		130		ns
ι _{rr}		$I_{\rm F} = 180 {\rm A}$ $V_{\rm R} = 400 {\rm V}$	$T_j = 125^{\circ}C$		170		115
Q _{rr}	Reverse Recovery Charge	$di/dt = 600 A/\mu s$	$T_j = 25^{\circ}C$		660		nC
			$T_{j} = 125^{\circ}C$		2760		ne



Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance Transistor Diode		Transistor			0.1	°C/W
R _{thJC}					0.32	C/ W	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Torque		For terminals	M5	2		3.5	19.111
Wt	Package Weight					300	g

SP6 Package outline (dimensions in mm)

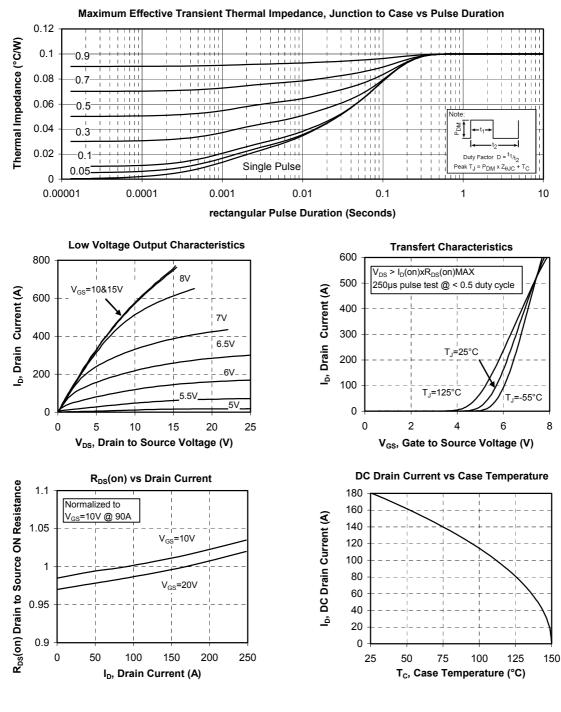


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

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Typical Performance Curve





Breakdown Voltage vs Temperature BV_{DSS}, Drain to Source Breakdown 1.2 Voltage (Normalized) 1.1 1.0 0.9 0.8 0.7 -50 -25 0 25 50 75 100 125 150 T_J, Junction Temperature (°C) Threshold Voltage vs Temperature 1.2 V_{GS}(TH), Threshold Voltage 1.1 1.0 (Normalized) 0.9 0.8 0.7 0.6 75 100 125 150 0 50 -50 -25 25 T_c, Case Temperature (°C) Capacitance vs Drain to Source Voltage 100000 Ciss C, Capacitance (pF) 10000 Coss 1000 Crss 100

10

0

10

20

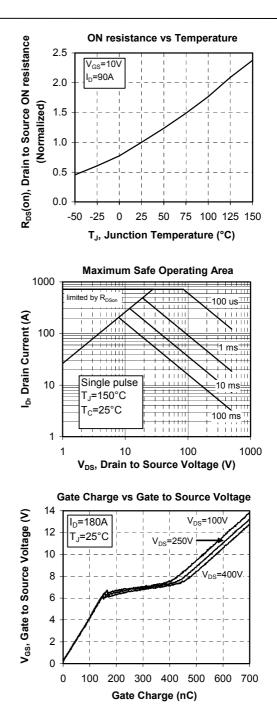
V_{DS}, Drain to Source Voltage (V)

30

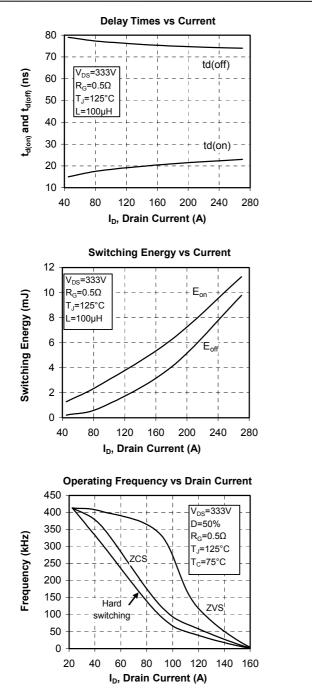
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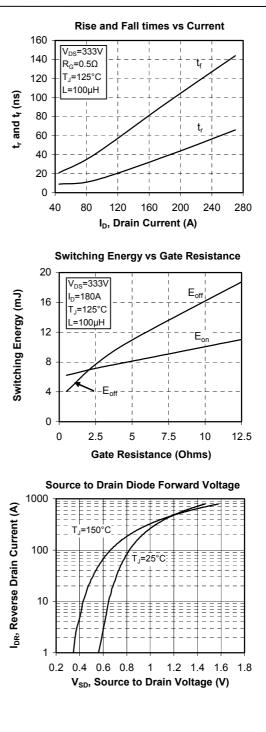
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